MAXIMUM RATINGS

Characteristics	Symbol	Value	Unit	
DC Supply Voltage		V _{CC}	-0.5 to +7.0	V
DC Input Voltage		VI	$-0.5 \leq V_I \leq +7.0$	V
DC Output Voltage Outp	ut in HIGH or LOW State (Note 1)	Vo	$-0.5 \le V_O \le 7.0$	V
DC Input Diode Current	V _I < GND	I _{IK}	-50	mA
DC Output Diode Current	I _{OK}	-50	mA	
DC Output Source/Sink Current		I _O	±50	mA
DC Supply Current Per Supply Pin		I _{CC}	±100	mA
DC Ground Current Per Ground Pin		I _{GND}	±100	mA
Storage Temperature Range	T _{STG}	-65 to +150	°C	
Power Dissipation in Still Air	SC-88, TSOP-6 (Note 2)	P_{D}	200	mW
Thermal Resistance	SC-88, TSOP-6 (Note 2)	θ_{JA}	333	°C/W
Lead temperature, 1 mm from Case for 10 Seconds		T _L	260	°C
Junction Temperature Under Bias		T _J	+150	°C
ESD Withstand Voltage	Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model (Note 5)	V _{ESD}	> 2000 > 200 N/A	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- I_O absolute maximum rating must be observed.
 Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
 Tested to EIA/JESD22-A114-A
- 4. Tested to EIA/JESD22-A115-A
- 5. Tested to JESD22-C101-A

RECOMMENDED OPERATING CONDITIONS

Par	ameter	Symbol	Min	Max	Unit
Supply Voltage	Operating Data Retention Only	V _{CC}	1.65 1.5	5.5 5.5	V
Input Voltage		VI	0	5.5	V
Output Voltage	(HIGH or LOW State)	Vo	0	5.5	V
Operating Free-Air Temperature		T _A	-55	+125	°C
Input Transition Rise or Fall Rate	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$ $V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	Δt/ΔV	0 0 0	20 10 5	ns/V

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	Т	T _A = 25°C		-55°C ≤ T	_ _A ≤ 125°C	
Parameter	Condition	Symbol	(V)	Min	Тур	Max	Min	Max	Unit
High-Level Input Voltage		V _{IH}	1.65-1.95	0.75 V _{CC}			0.75 V _{CC}		٧
			2.3 to 5.5	0.7 V _{CC}			0.7 V _{CC}		
Low-Level Input Voltage		V _{IL}	1.65–1.95			0.25 V _{CC}		0.25 V _{CC}	V
			2.3 to 5.5			0.3 V _{CC}		0.3 V _{CC}	
High-Level Output	I _{OH} = -100 μA	V _{OH}	1.65 to 5.5	V _{CC} - 0.1	V_{CC}		V _{CC} - 0.1		V
Voltage V _{IN} = V _{IL}	I _{OH} = -3 mA		1.65	1.29	1.52		1.29		
· IIV · IL	I _{OH} = -8 mA		2.3	1.9	2.1		1.9		
	I _{OH} = -12 mA		2.7	2.2	2.4		2.2		
	I _{OH} = -16 mA		3.0	2.4	2.7		2.4		
	I _{OH} = -24 mA		3.0	2.3	2.5		2.3		
	I _{OH} = -32 mA		4.5	3.8	4.0		3.8		
Low-Level Output	I _{OL} = 100 μA	V _{OL}	1.65 to 5.5			0.1		0.1	V
Voltage V _{IN} = V _{IH}	I _{OL} = 3 mA		1.65		0.08	0.24		0.24	
- 1111 - 1171	I _{OL} = 8 mA		2.3		0.20	0.3		0.3	
	I _{OL} = 12 mA		2.7		0.22	0.4		0.4	
	I _{OL} = 16 mA		3.0		0.28	0.4		0.4	
	I _{OL} = 24 mA		3.0		0.38	0.55		0.55	
	I _{OL} = 32 mA		4.5		0.42	0.55		0.55	
Input Leakage Current	V _{IN} = V _{CC} or GND	I _{IN}	0 to 5.5			±0.1		±1.0	μΑ
Power Off-Output Leakage Current	V _{OUT} = 5.5 V	I _{OFF}	0			1		10	μΑ
Quiescent Supply Current	V _{IN} = V _{CC} or GND	Icc	1.65 to 5.5			1		10	μΑ

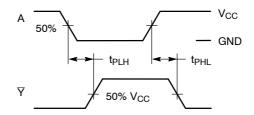
AC ELECTRICAL CHARACTERISTICS t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 Ω

			V _{CC}	T _A = 25°C		-55 °C ≤ T_A ≤ 125°C			
Parameter	Condition	Symbol	(V)	Min	Тур	Max	Min	Max	Unit
Propagation Delay	$R_L = 1 M\Omega, C_L = 15 pF$	t _{PLH}	1.65	1.8	2.3	9.2	1.8	11.0	ns
(Figure 3 and 4)	$R_L = 1 M\Omega, C_L = 15 pF$	^t PHL	1.8	1.8	4.4	7.6	1.8	8.4	
	$R_L = 1 \text{ M}\Omega, C_L = 15 \text{ pF}$		2.5 ± 0.2	1.2	3.0	5.1	1.2	5.6	
	R_L = 1 M Ω , C_L = 15 pF		3.3 ± 0.3	0.8	2.2	3.4	0.8	3.8	
	$R_L = 500 \Omega, C_L = 50 pF$			1.2	2.9	4.5	1.2	5.0	
	R_L = 1 M Ω , C_L = 15 pF		5.0 ± 0.5	0.5	18	2.8	0.5	3.1	
	$R_L = 500 \Omega, C_L = 50 pF$	1		0.8	2.3	3.6	0.8	4.0	

CAPACITIVE CHARACTERISTICS

Parameter	Symbol	Condition	Typical	Unit
Input Capacitance	C _{IN}	V_{CC} = 5.5 V, V_{I} = 0 V or V_{CC}	2.5	pF
Power Dissipation Capacitance (Note 6)	C _{PD}	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC} 10 MHz, V_{CC} = 5.5 V, V_{I} = 0 V or V_{CC}	9 11	pF

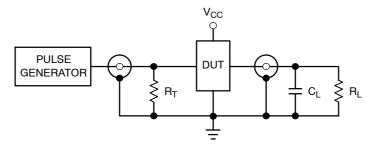
^{6.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.



PROPAGATION DELAYS

 t_R = t_F = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns

Figure 3. Switching Waveforms



 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

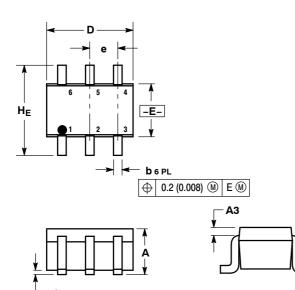
ORDERING INFORMATION

Device	Package	Shipping [†]
NL27WZ04DFT2	SC-88/SC70-6/SOT-363	
NL27WZ04DFT2G	SC-88/SC70-6/SOT-363 (Pb-Free)	3000 / Tape & Reel
NL27WZ04DTT1	TSOP-6	— Sooo / Tape & neel
NL27WZ04DTT1G	TSOP-6 (Pb-Free)	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

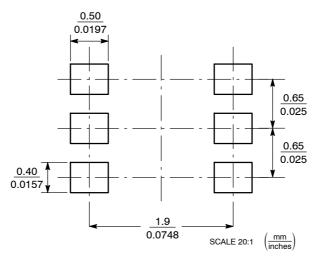
SC-88/SC70-6/SOT-363 CASE 419B-02 **ISSUE W**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	MILLIMETERS				INCHES	3	
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.80	0.95	1.10	0.031	0.037	0.043	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
А3		0.20 RE	F	0.008 REF			
b	0.10	0.21	0.30	0.004	0.008	0.012	
С	0.10	0.14	0.25	0.004	0.005	0.010	
D	1.80	2.00	2.20	0.070	0.078	0.086	
Е	1.15	1.25	1.35	0.045	0.049	0.053	
е		0.65 BS	С	0.026 BSC			
L	0.10	0.20	0.30	0.004	0.008	0.012	
HE	2.00	2.10	2.20	0.078	0.082	0.086	

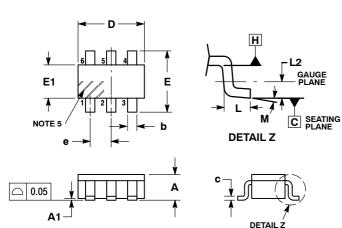
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSOP-6 CASE 318G-02 **ISSUE U**

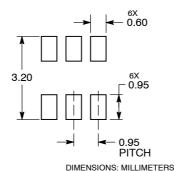


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR
 GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D
 AND E1 ARE DETERMINED AT DATUM H.
- 5. PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

	MILLIMETERS						
DIM	MIN	NOM	MAX				
Α	0.90	1.00	1.10				
A1	0.01	0.06	0.10				
b	0.25	0.38	0.50				
С	0.10	0.18	0.26				
D	2.90	3.00	3.10				
E	2.50	2.75	3.00				
E1	1.30	1.50	1.70				
е	0.85	0.95	1.05				
L	0.20	0.40	0.60				
L2	0.25 BSC						
М	0°	-	10°				

RECOMMENDED SOLDERING FOOTPRINT*



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